



High Voltage Transistors

FEATURE

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBT5550LT1G S-LMBT5550LT1G	M1F	3000/Tape&Reel
LMBT5550LT3G S-LMBT5550LT3G	M1F	10000/Tape&Reel
LMBT5551LT1G S-LMBT5551LT1G	G1	3000/Tape&Reel
LMBT5551LT3G S-LMBT5551LT3G	G1	10000/Tape&Reel

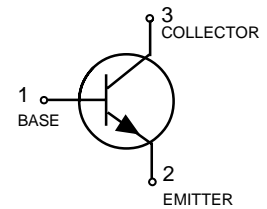
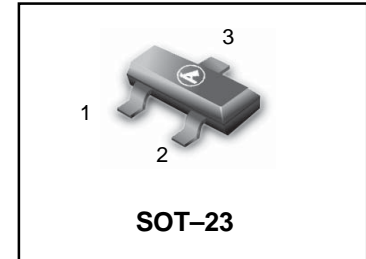
MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector - Emitter Voltage	MMBT5550 MMBT5551	V_{CEO}	140	Vdc
			160	
Collector - Base Voltage	MMBT5550 MMBT5551	V_{CBO}	160	Vdc
			180	
Emitter - Base Voltage		V_{EBO}	6.0	Vdc
Collector Current - Continuous		I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

LMBT5550LT1G
LMBT5551LT1G
S-LMBT5550LT1G
S-LMBT5551LT1G





LMBT5550LT1G LMBT5551LT1G S-LMBT5550LT1G S-LMBT5551LT1G

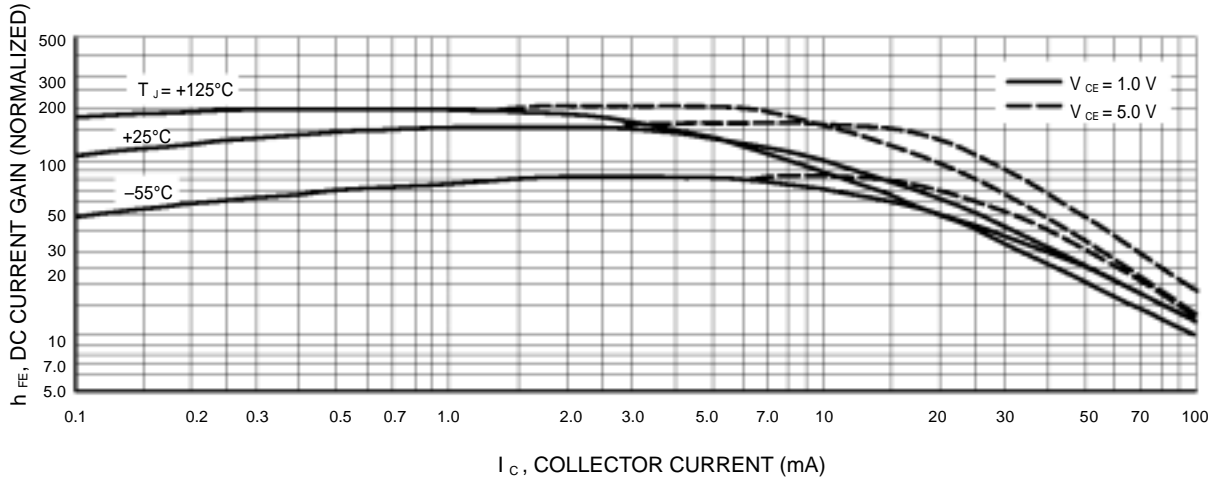
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (Note 3) ($I_C = 1.0 \text{ mAdc}$, $I_B = 0$)	LMBT5550 LMBT5551	$V_{(BR)CEO}$	140 160	- -	Vdc
Collector - Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}$, $I_E = 0$)	LMBT5550 LMBT5551	$V_{(BR)CBO}$	160 180	- -	Vdc
Emitter - Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}$, $I_C = 0$)		$V_{(BR)EBO}$	6.0	-	Vdc
Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 120 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$) ($V_{CB} = 120 \text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	LMBT5550 LMBT5551 LMBT5550 LMBT5551	I_{CBO}	- - - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}$, $I_C = 0$)		I_{EBO}	-	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	LMBT5550 LMBT5551 LMBT5550 LMBT5551 LMBT5550 LMBT5551	h_{FE}	60 80 60 80 20 30	- - 250 250 - -	-
Collector - Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	Both Types LMBT5550 LMBT5551	$V_{CE(sat)}$	- - -	0.15 0.25 0.20	Vdc
Base - Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	Both Types LMBT5550 LMBT5551	$V_{BE(sat)}$	- - -	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off ($V_{CB} = 10 \text{ V}$) ($V_{CB} = 75 \text{ V}$)	Both Types	I_{CES}	- -	50 100	nA

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.
3. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

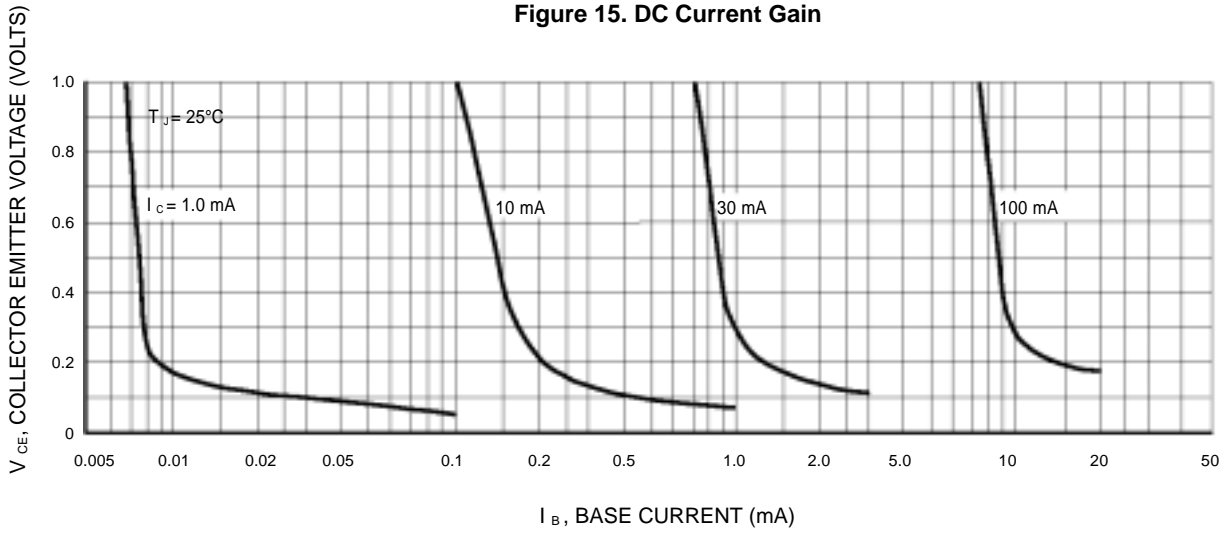


**LMBT5550LT1G LMBT5551LT1G
S-LMBT5550LT1G S-LMBT5551LT1G**



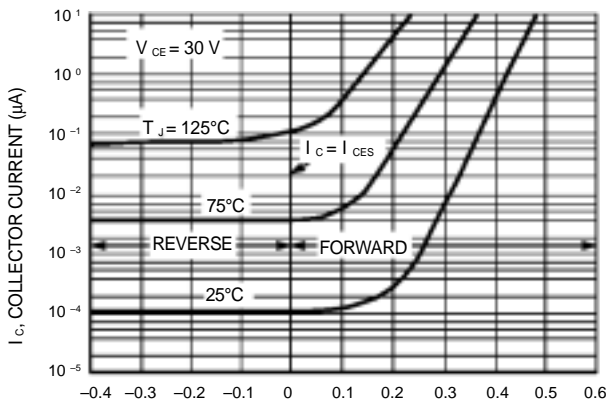
I_C , COLLECTOR CURRENT (mA)

Figure 15. DC Current Gain



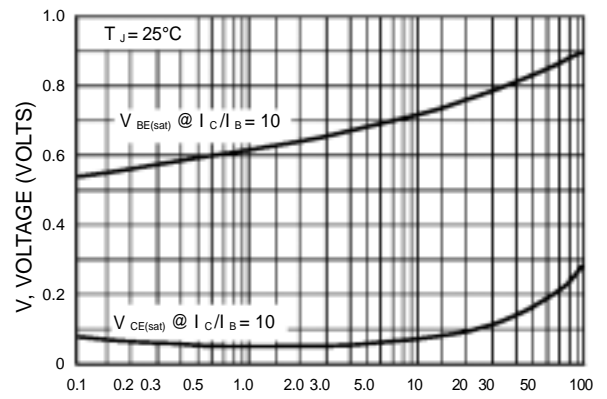
I_B , BASE CURRENT (mA)

Figure 16. Collector Saturation Region



V_{BE} , BASE-EMITTER VOLTAGE (VOLTS)

Figure 3. Collector Cut-Off Region



I_C , COLLECTOR CURRENT (mA)

Figure 4. "On" Voltages



**LMBT5550LT1G LMBT5551LT1G
S-LMBT5550LT1G S-LMBT5551LT1G**

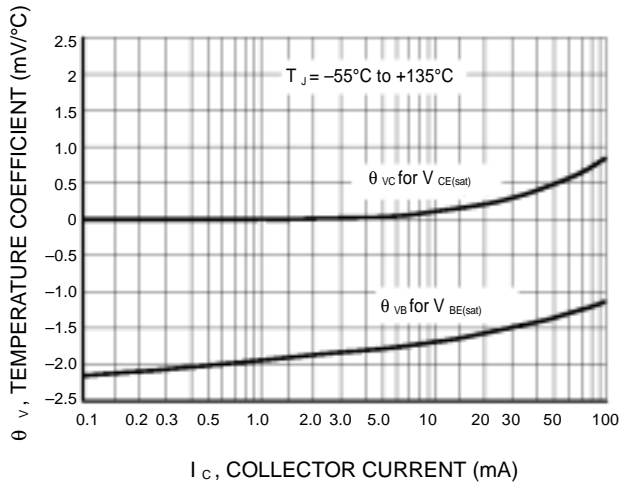
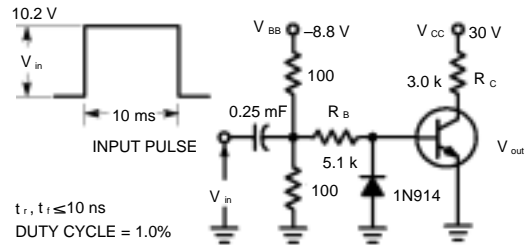


Figure 5. Temperature Coefficients



Values Shown are for $I_C @ 10 \text{ mA}$
Figure 6. Switching Time Test Circuit

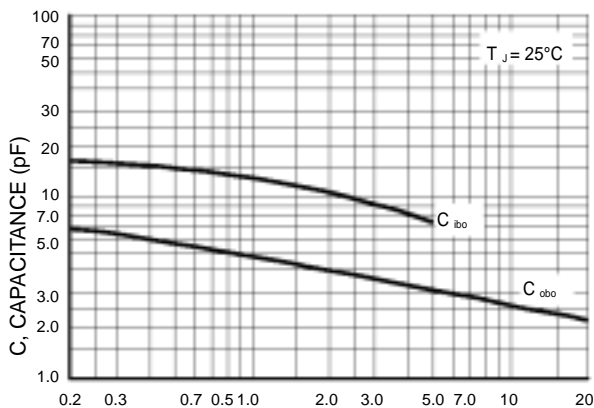
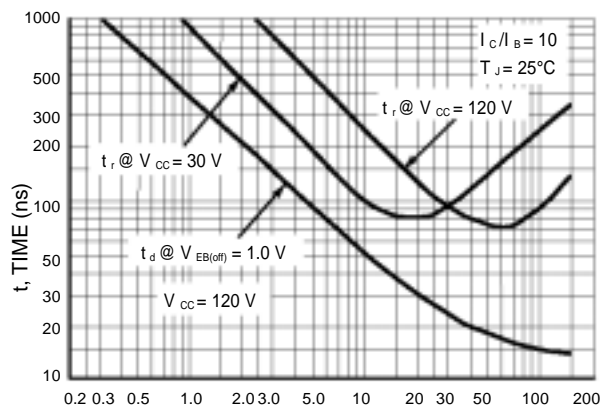


Figure 7. Capacitances Figure



8. Turn-On Time

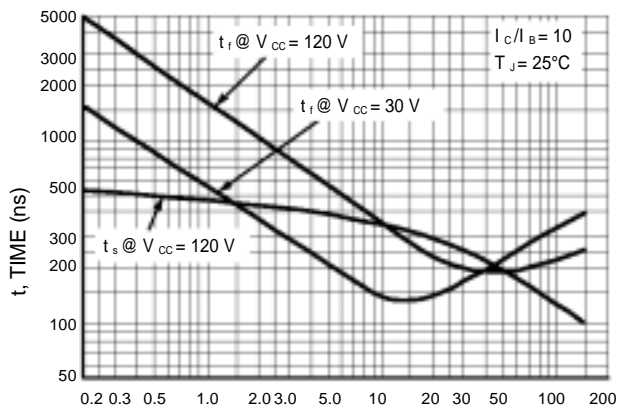
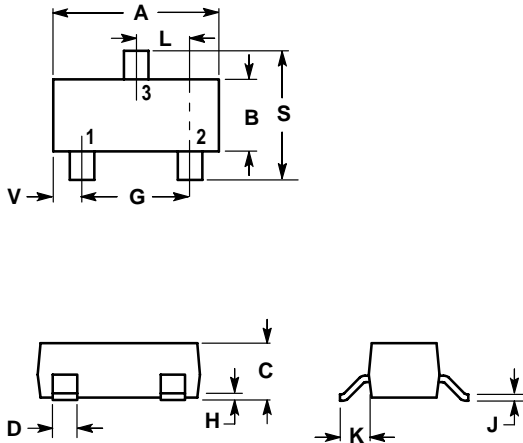


Figure 9. Turn-Off Time



**LMBT5550LT1G LMBT5551LT1G
S-LMBT5550LT1G S-LMBT5551LT1G**

SOT-23

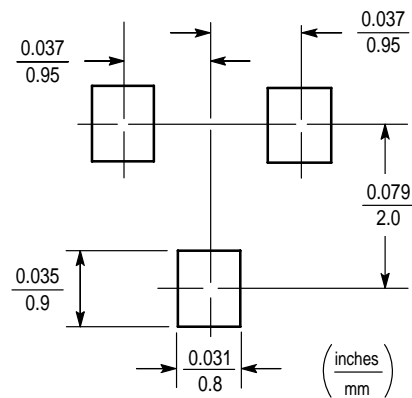


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR



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